SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

Features

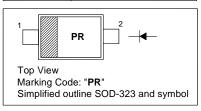
- Small surface mounting type
- Low forward voltage
- High reliability

Applications

• Low power rectification

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25$ °C)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	40	V
Reverse Voltage	V_R	20	V
Average Forward Current	Io	0.5	А
Peak Forward Surge Current	I _{FSM}	3	А
Junction Temperature	T _j	125	°C
Storage Temperature Range	Ts	- 40 to + 125	°C

Characteristics at T_a = 25 °C

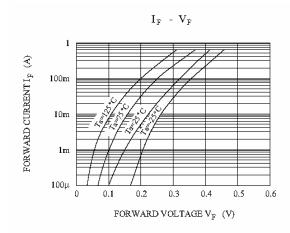
Parameter	Symbol	Тур.	Max.	Unit
Forward Voltage at $I_F = 10 \text{ mA}$ at $I_F = 500 \text{ mA}$	V _F		0.3 0.5	V
Reverse Current at $V_R = 10 \text{ V}$ at $V_R = 40 \text{ V}$	I _R	-	30 200	μΑ
Total Capacitance at $V_R = 10 \text{ V}$, $f = 1 \text{ MHz}$	Ст	20	-	pF

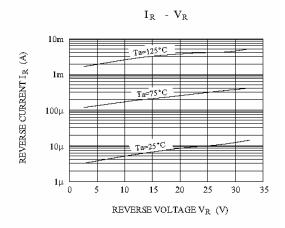


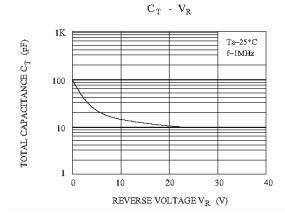




















PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323

